MEMORY IP

SRAM IP

Differentiated Features

Remarkable Features of Renesas SRAM and TCAM IP.

- Small area
  - By optimizing the peripheral circuit of memory, particularly small area is realized.
- Low power
  - Support low leak retention mode (Resume Standby) and power off mode (Shut down).
- IDM-oriented design quality
  - Many product proven.

SRAM IP Portfolio

Foundry	Node	Cell Type	Port Type					
			1WR	2CLK		1CLK		1WR 1.8-3.3V
				1W1R	2WR	1W1R	2WR	
TSMC	40LP	-	✓	✓	✓			✓
	28HPL	-	✓		✓	✓		
	28 HPC	LL	✓	✓	✓	✓		
		GL						
	28 HPC+	ULL	✓	✓	✓	✓	✓	
		GL	✓	✓	✓	✓	✓	
	16FF+	LL	✓	✓	✓	✓		
	16FFC	LL	✓	✓	✓	✓		
	12FFC	LL	✓	✓	✓	✓		
	7FF	-	✓	✓				

Note:
- IP under development which has not been listed may also be available, so please contact us.
- 1WR -> 1 write/read port(single port) SRAM
- 1W1R -> 1write port and 1 read port(2port) SRAM
- 2WR -> 2 write/read ports(dual port) SRAM
- 1WR 1.8-3.3V -> 1 write/read port(single port) SRAM using thick gate transistor.

These IPs are contract design IP. Please contact for detail.

R06PF0042EJ0100

2022.12

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